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(54) **Title:** PULSED ULTRA-HIGH ASPECT RATIO DIELECTRIC ETCH

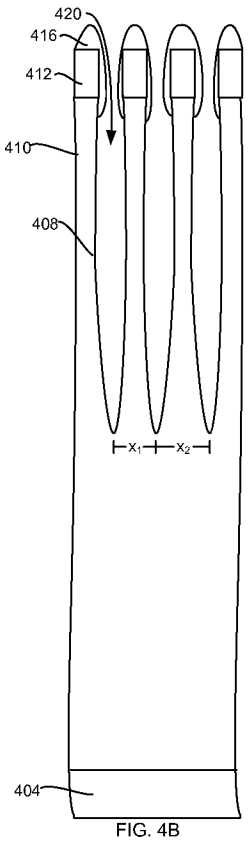


FIG. 4B

(57) **Abstract:** A method for selectively etching an ultra high aspect ratio feature dielectric layer through a carbon based mask in an etch chamber is provided. A flow of an etch gas is provided, comprising a fluorocarbon containing molecule and an oxygen containing molecule to the etch chamber. A pulsed bias RF signal is provided. An energizing RF signal is provided to transform the etch gas to a plasma.

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